

NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE60P14AK uses advanced trench technology and design to provide excellent $R_{\text{DS(ON)}}$ with low gate charge .This device is well suited for use as a load switch or in PWM applications.

General Features

V_{DS} =-60V,I_D =-14A

 $R_{DS(ON)}$ <75m Ω @ V_{GS} =-10V

 $R_{DS(ON)}$ <96m Ω @ V_{GS} =-4.5V

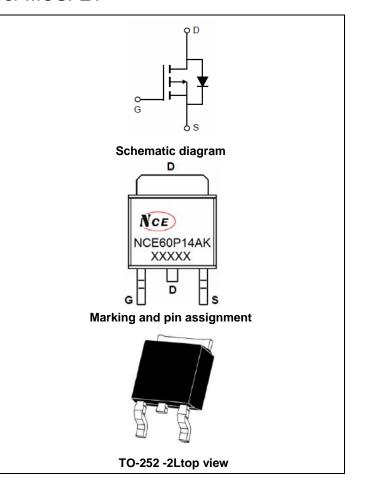
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Application

- Load switch
- PWM application

100% UIS TESTED!

100% AVds TESTED!



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE60P14AK	NCE60P14AK	TO-252-2L	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	-60	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	-14	А
Pulsed Drain Current	I _{DM}	-56	А
Maximum Power Dissipation	P _D	50	W
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	$^{\circ}$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{ heta JC}$	3.0	°C/W
--	----------------	-----	------

Electrical Characteristics (T_C=25 °C unless otherwise noted)

Parameter	Parameter Symbol Condition		Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA -60		-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V,V _{GS} =0V	-	-	-1	μΑ
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =-250μA	-1.0	1.5	-2.0	V
Drain-Source On-State Resistance	5	V_{GS} =-10V, I_D =-14A	-	63	75	mΩ
Diam-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-10A	-	74	96	mΩ
Forward Transconductance	g FS	V _{DS} =-5V,I _D =-14A	-	10	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	\/ 20\/\/ 0\/	-	930	-	PF
Output Capacitance	Coss	V_{DS} =-30V, V_{GS} =0V, F=1.0MHz	-	85	-	PF
Reverse Transfer Capacitance	C _{rss}	r=1.0lvln2	-	35	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	8	-	nS
Turn-on Rise Time	t _r	V_{DD} =-30V, R_L =2 Ω ,	-	4	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =-10 V , R_{G} =3 Ω	-	32	-	nS
Turn-Off Fall Time	t _f		-	7	-	nS
Total Gate Charge	Qg	V 00 L 44A	-	25	-	nC
Gate-Source Charge	Q_{gs}	V _{DS} =-30,I _D =-14A,	-	3	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =-10V	-	7	-	nC
Drain-Source Diode Characteristics	1					I.
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-14A	-		-1.2	V
Diode Forward Current (Note 2)	Is		-	-	-14	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =- 14A	-	25		nS
Reverse Recovery Charge	Qrr	$di/dt = -100A/\mu s^{(Note3)}$	-	31		nC

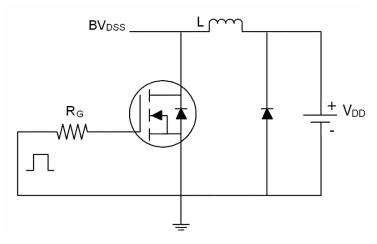
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production

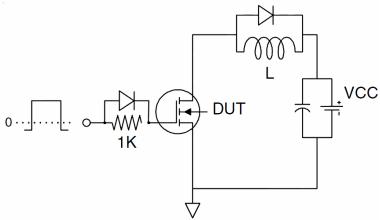


Test Circuit

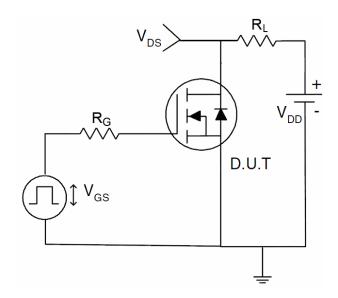
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics (Curves)

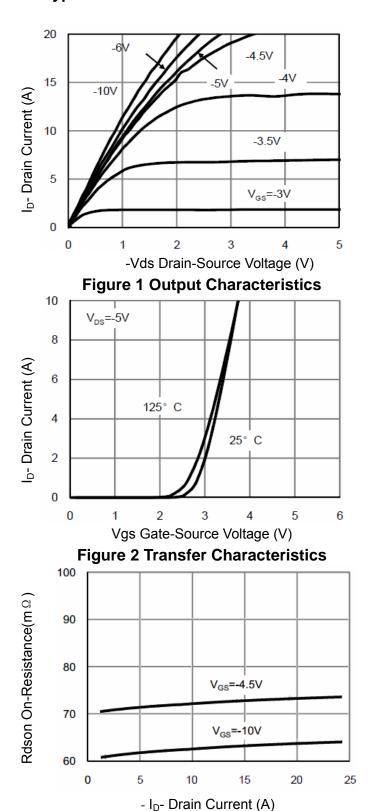


Figure 3 Rdson- Drain Current

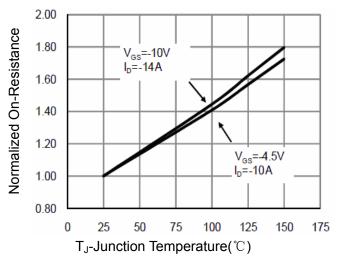
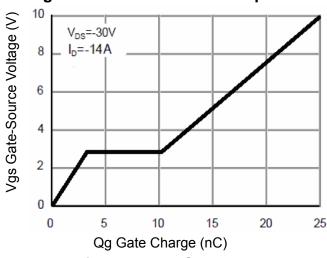


Figure 4 Rdson-Junction Temperature



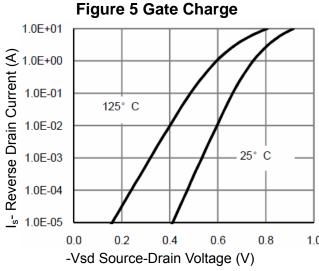
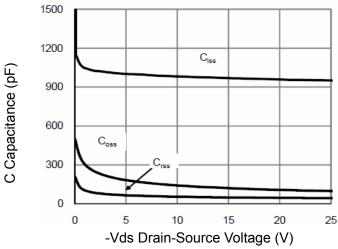


Figure 6 Source- Drain Diode Forward





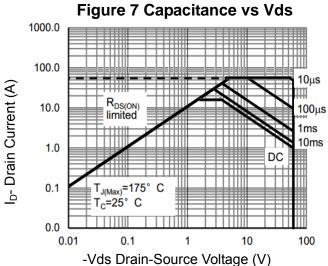
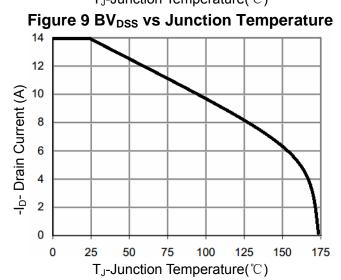


Figure 8 Safe Operation Area



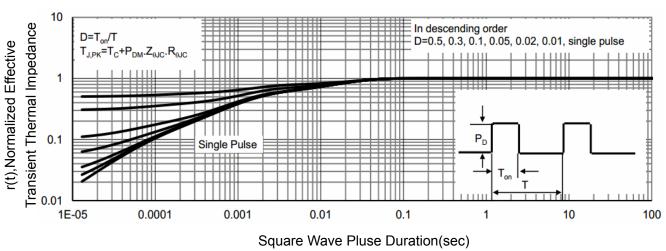
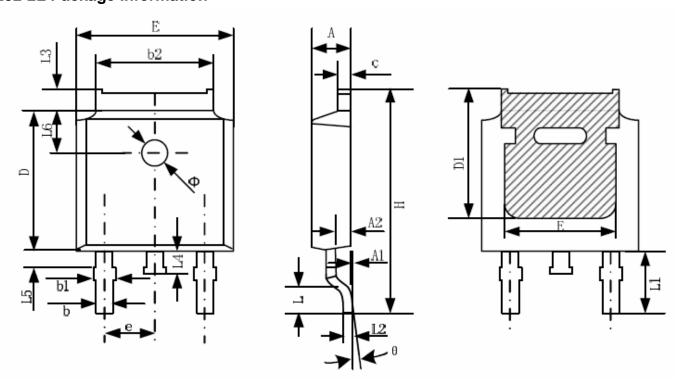


Figure 10 ID Current De-rating

Figure 11 Normalized Maximum Transient Thermal Impedance



TO-252-2L Package Information



Cumhal	Dimensions	n Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	2.20	2.38	0.087	0.094	
A1	0.00	0.10	0.000	0.004	
A2	0.90	1.10	0.035	0.043	
b	0.72	0.85	0.028	0.033	
b1	0.72	0.90	0.028	0.035	
b2	5.13	5.46	0.202	0.215	
С	0.47	0.60	0.019	0.024	
D	6.00	6.20	0.236	0.244	
D1	5.25		0.207		
Е	6.50	6.70	0.256	0.264	
E1	4.70		0.185		
e	2.19	2.39	0.086	0.094	
Н	9.80	10.40	0.386	0.409	
L	1.40	1.70	0.055	0.067	
L1	2.90 REF		0.114 REF		
L2	0.508 BSC		0.020 BSC		
L3	0.90	1.25	0.035	0.049	
L4	0.60	1.00	0.024	0.039	
L5	0.15	0.75	0.006	0.030	
L6	1.80	REF	0.071 REF		
Φ	1.20	1.40	0.047	0.055	
θ	0°	8°	0°	8°	

http://www.ncepower.com

NCE60P14AK

Attention

- Any and all NCE power products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your NCE power representative nearest you before using any NCE power products described or contained herein in such applications.
- NCE power assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all NCE power products described or contained herein.
- Specifications of any and all NCE power products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- NCE power Semiconductor CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all NCE power products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of NCE power Semiconductor CO.,LTD.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. NCE power believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the NCE power product that you intend to use.
- This catalog provides information as of Sep.2010. Specifications and information herein are subject to change without notice.